

# **HD74HC166**

## Parallel-load 8-bit Shift Register

REJ03D0582-0300 Rev.3.00 Jan 31, 2006

#### **Description**

This device is an 8-bit shift register with an output from the last stage. Data may be loaded into the register either in parallel or in serial form. When the Shift/Load input is low, the data is loaded asynchronously in parallel. When the Shift/Load input is high, the data is loaded serially on the rising edge of either clock inhibit or Clock. Clear is asynchronous and active-low.

The 2-input NOR clock may be used either by combining two independent clock sources or by designating one of the clock inputs to act as a clock inhibit.

#### **Features**

• High Speed Operation:  $t_{pd}$  (Clock to  $Q_H$ ) = 14 ns typ ( $C_L$  = 50 pF)

• High Output Current: Fanout of 10 LSTTL Loads

• Wide Operating Voltage:  $V_{CC} = 2$  to 6 V

• Low Input Current: 1 μA max

• Low Quiescent Supply Current:  $I_{CC}$  (static) = 4  $\mu$ A max (Ta = 25°C)

• Ordering Information

Part Name	Package Type	Package Code (Previous Code)	Package Abbreviation	Taping Abbreviation (Quantity)
HD74HC166P	DILP-16 pin	PRDP0016AE-B (DP-16FV)	Р	_
HD74HC166FPEL	SOP-16 pin (JEITA)	PRSP0016DH-B (FP-16DAV)	FP	EL (2,000 pcs/reel)

Note: Please consult the sales office for the above package availability.

#### **Function Table**

		Clock			Parallel	Internal	Internal outputs		
Clear	Shift/Load	Inhibit	Clock	Serial	A H	$Q_A$	Q <sub>B</sub>	Q <sub>H</sub>	
L	Х	Х	Χ	Х	Х	L	L	L	
Н	Х	L	L	Х	Х	Q <sub>A0</sub>	Q <sub>B0</sub>	Q <sub>H0</sub>	
Н	L	L	$\int$	Х	a h	а	b	h	
Н	Н	L		Н	Χ	Н	$Q_{An}$	$Q_{Gn}$	
Н	Н	L		L	Χ	L	$Q_{An}$	$Q_{Gn}$	
Н	Х	Н		Х	Х	$Q_{A0}$	$Q_{B0}$	Q <sub>H0</sub>	

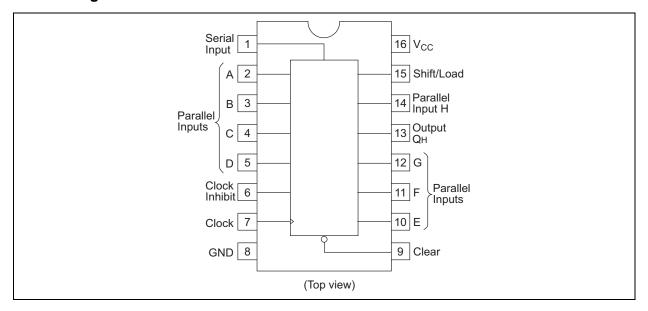
 $Q_{Ao}$  to  $Q_{Ho}$  = Outputs remain unchanged.

Q<sub>An</sub> to Q<sub>Gn</sub> = Data shifted from the previous stage on a positive edge at the clock input.

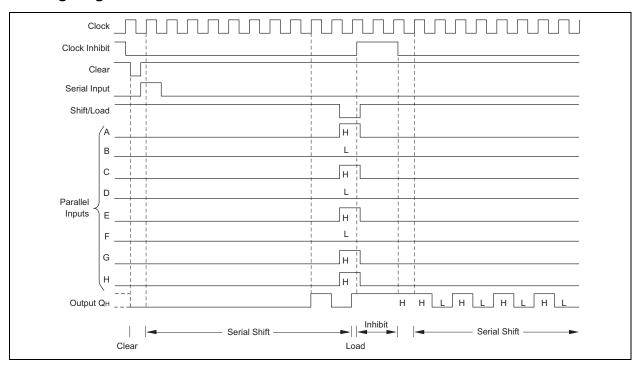
H: High levelL: Low levelX: Irrelevant



### **Pin Arrangement**



### **Timing Diagram**



### **Absolute Maximum Ratings**

Item	Symbol	Ratings	Unit
Supply voltage range	V <sub>CC</sub>	-0.5 to 7.0	V
Input / Output voltage	Vin, Vout	–0.5 to V <sub>CC</sub> +0.5	V
Input / Output diode current	$I_{IK}$ , $I_{OK}$	±20	mA
Output current	Io	±25	mA
V <sub>CC</sub> , GND current	I <sub>CC</sub> or I <sub>GND</sub>	±50	mA
Power dissipation	P <sub>T</sub>	500	mW
Storage temperature	Tstg	-65 to +150	°C

Note: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

### **Recommended Operating Conditions**

Item Symbol		Ratings	Unit	Conditions	
Supply voltage	V <sub>CC</sub>	2 to 6	V		
Input / Output voltage	V <sub>IN</sub> , V <sub>OUT</sub>	0 to V <sub>CC</sub>	V		
Operating temperature	Та	-40 to 85	°C		
		0 to 1000		V <sub>CC</sub> = 2.0 V	
Input rise / fall time*1	t <sub>r</sub> , t <sub>f</sub>	0 to 500	ns	V <sub>CC</sub> = 4.5 V	
		0 to 400		V <sub>CC</sub> = 6.0 V	

Note: 1. This item guarantees maximum limit when one input switches.

Waveform: Refer to test circuit of switching characteristics.

#### **Electrical Characteristics**

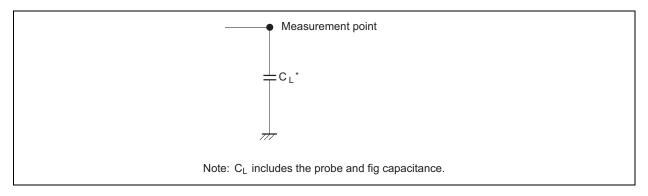
			Т	a = 25°	С	Ta = -40 to+85°C				
Item	Symbol	V <sub>cc</sub> (V)	Min	Тур	Max	Min	Max	Unit	Test Conditions	
Input voltage	V <sub>IH</sub>	2.0	1.5	_	_	1.5	_	V		
		4.5	3.15	_	_	3.15	_			
		6.0	4.2	_	_	4.2	_			
	$V_{IL}$	2.0	_	_	0.5	_	0.5	V		
		4.5	_	_	1.35	_	1.35			
		6.0	_	_	1.8	_	1.8			
Output voltage	V <sub>OH</sub>	2.0	1.9	2.0	_	1.9	_	V	Vin = $V_{IH}$ or $V_{IL}$ $I_{OH} = -20 \mu$	Α
		4.5	4.4	4.5	_	4.4	_			
		6.0	5.9	6.0	_	5.9	_			
		4.5	4.18	_	_	4.13	_		$I_{OH} = -4 \text{ m/s}$	A
		6.0	5.68	_	_	5.63	_		I <sub>OH</sub> = −5.2 ı	mΑ
	V <sub>OL</sub>	2.0	_	0.0	0.1	_	0.1	V	Vin = $V_{IH}$ or $V_{IL}$ $I_{OL} = 20 \mu A$	,
		4.5	_	0.0	0.1	_	0.1			
		6.0	_	0.0	0.1	_	0.1			
		4.5	_	_	0.26	_	0.33		$I_{OL} = 4 \text{ mA}$	
		6.0	_	_	0.26	_	0.33		$I_{OL} = 5.2 \text{ m}$	Α
Input current	lin	6.0	_	_	±0.1		±1.0	μΑ	Vin = V <sub>CC</sub> or GND	
Quiescent supply current	I <sub>CC</sub>	6.0	_	_	4.0	_	40	μΑ	Vin = $V_{CC}$ or GND, lout = $0 \mu A$	

### **Switching Characteristics**

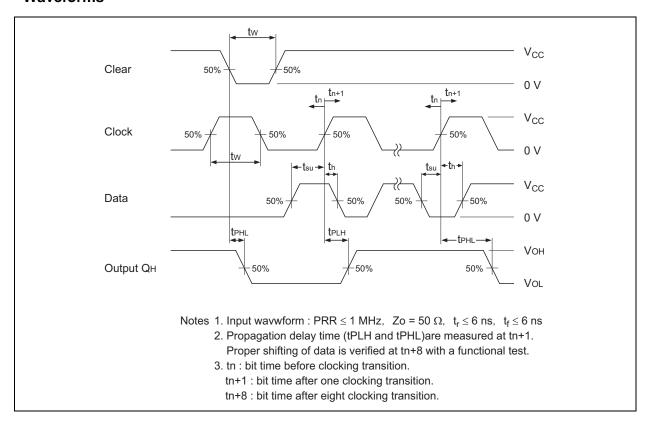
 $(C_L = 50 \text{ pF}, \text{Input } t_r = t_f = 6 \text{ ns})$ 

	1	1				1			$C_L = 50 \text{ pr}$ , input $t_r = t_f = 0$
			Т	Ta = $25^{\circ}$ C Ta = $-40 \text{ to } +85^{\circ}$ C					
Item	Symbol	V <sub>CC</sub> (V)	Min	Тур	Max	Min	Max	Unit	Test Conditions
Maximum clock	f <sub>max</sub>	2.0	_	_	5	_	4	MHz	
frequency		4.5	_		25	_	20		
		6.0	_	_	29	_	24		
Propagation delay	$t_{PHL}$ , $t_{PLH}$	2.0			175	_	220	ns	Clock to Q <sub>H</sub>
time		4.5	_	14	35	_	44		
		6.0		_	30	_	37		
	t <sub>PHL</sub>	2.0		_	150	_	190	ns	Clear to Q <sub>H</sub>
		4.5		12	30	_	38		
		6.0			26	_	33		
Setup time	t <sub>su</sub>	2.0	150	_	_	190	_	ns	Shift/Load to Clock
		4.5	30	2	_	38	_		
		6.0	26	_	_	33	_		
		2.0	100	_	_	125	_	ns	Data to Clock
		4.5	20	1	_	25	_		
		6.0	17	_	_	21	_		
Hold time	t <sub>h</sub>	2.0	5	_	_	5	_	ns	Clock to Data
		4.5	5	0	_	5	_		
		6.0	5	_	_	5	_		
Pulse width	t <sub>w</sub>	2.0	80	_	_	100	_	ns	Clock, Clear
		4.5	16	6	_	20	_		
		6.0	14	_	_	17			
Output rise/fall	t <sub>TLH</sub> , t <sub>THL</sub>	2.0		_	75	_	95	ns	
time		4.5		5	15	_	19		
		6.0		_	13	_	16		
Input capacitance	Cin	_	_	5	10	_	10	pF	

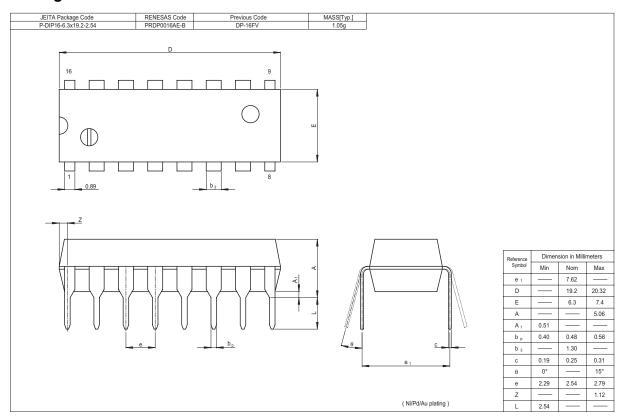
#### **Test Circuit**

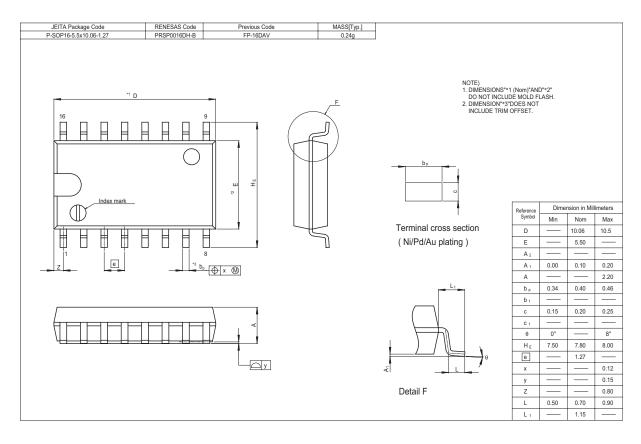


#### **Waveforms**



### **Package Dimensions**





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